

Bi-directional 5V Ultra Small Capacitance ESD

Features

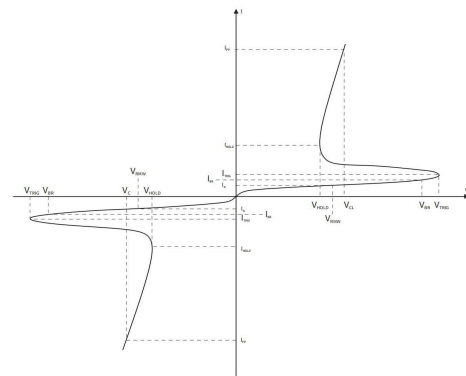
- ## Applications

- Reverse Working Voltage**
5V Max.
Low capacitance
0.45pF(Max.)



SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{ESD}	Electrostatic Discharge Voltage	ESD per IEC 61000-4-2(Air)	±25	KV
		ESD per IEC 61000-4-2(Contact)	±23	KV
P _{PP}	Peak Pulse Power	tp = 8/20 μs	72	W
I _{PP}	Rated Peak Pulse Current	tp = 8/20 μs	9.0	A
T _J	Operating JunctionTemperature Range	—	-55 to +125	°C
T _{STG}	Operating JunctionTemperature Range	—	-55 to +150	°C

SYMBOL	PARAMETER
I_{PP}	Peak Pulse Current @8/20 μ s
V_C	Clamping Voltage @ I_{PP}
I_{BR} / I_T	Test Current
V_{BR}	Breakdown Voltage @ I_T
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
I_{TRIG}	Reverse Trigger Current
V_{TRIG}	Reverse Trigger Voltage
I_{HOLD}	Reverse Holding Current
V_{HOLD}	Reverse Holding Voltage
P_{PP}	Peak Pulse Power Dissipation

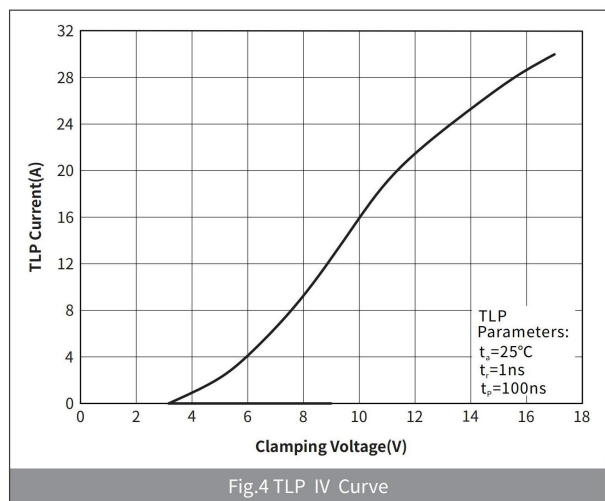
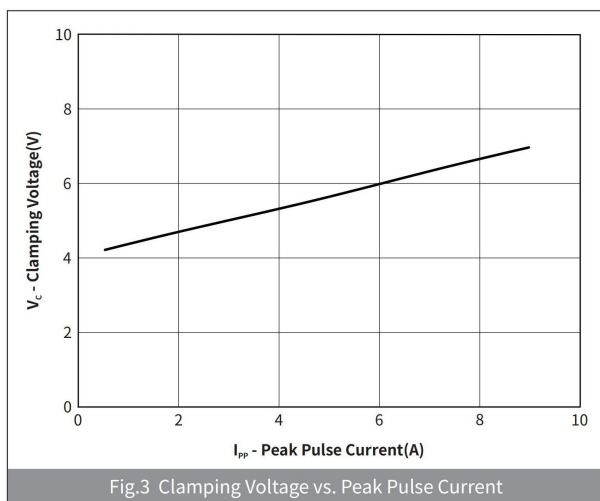
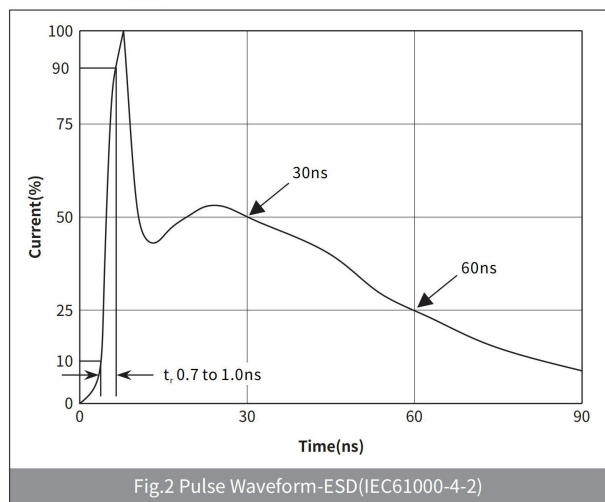
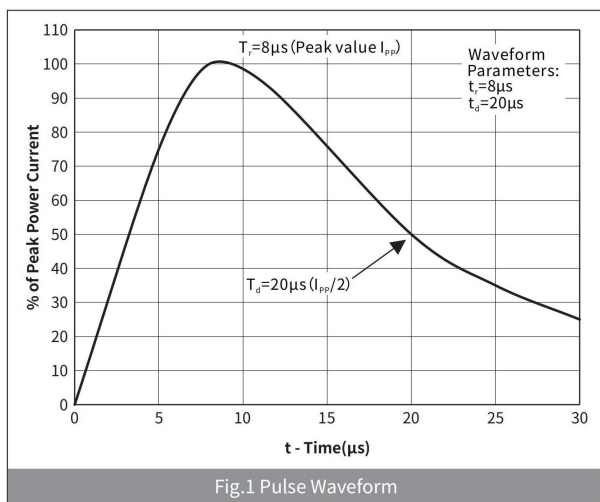


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Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	CONDITION	Min	Typ	Max	UNIT
Peak Reverse Working Voltage	V_{RWM}	$T_a=25^\circ\text{C}$	—	—	5.0	V
Breakdown Voltage	V_{BR}	$I_R=1\text{mA}, T_a=25^\circ\text{C}$	6.0	—	—	V
Reverse Leakage Current	I_R	$V_R=5\text{V}, T_a=25^\circ\text{C}$	—	—	0.5	μA
Dynamic Resistance	R_{DYN}	$Z_0=50\Omega$, calculated from 4A to 16A	—	0.35	—	Ω
TLP Clamping Voltage	$V_C@TLP$	$Z_0=50\Omega, t_p=100\text{ns}, t_r=1\text{ns}; TLP@16\text{A}$	—	10.0	—	V
Clamping Voltage	V_C	$I_{PP}=9\text{A}, t_p=8/20\mu\text{s}$	—	—	8.0	V
Junction Capacitance	C_J	$V_R=0\text{V}, f=1\text{MHz}$	—	—	0.45	pF

Ratings And Characteristics Curves (Ta=25°C Unless otherwise specified)

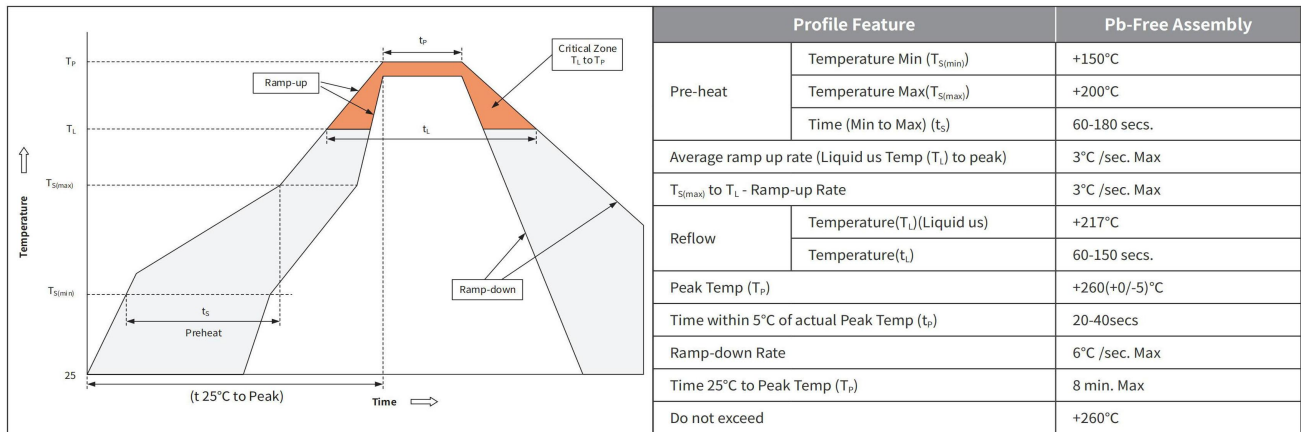


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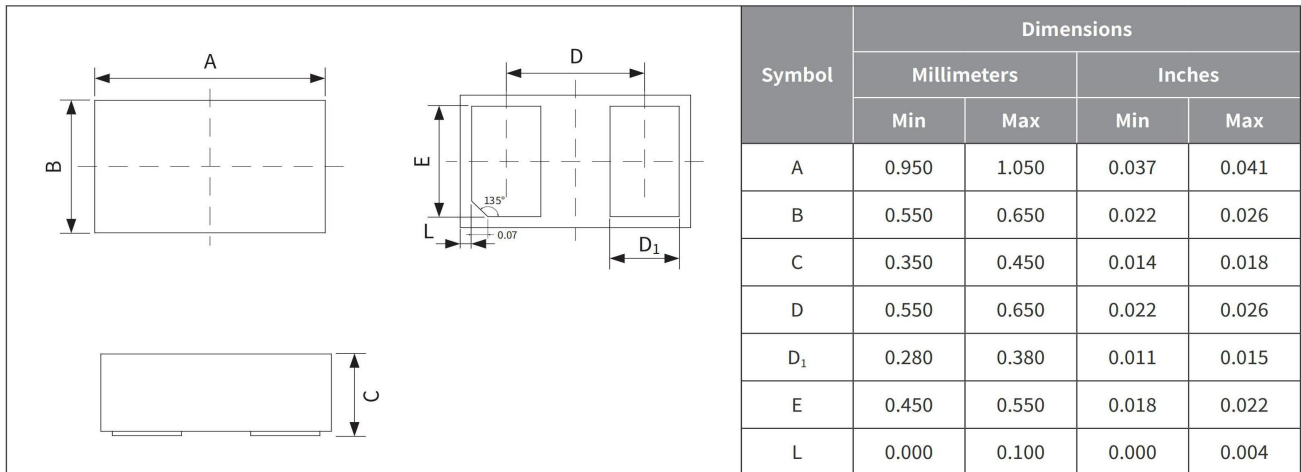
Ordering Information

PREFERRED P/N	PACKAGE	SIZE(mm)	DELIVERY MODE	MPQ(PCS)
	DFN1006-2L	1.00×0.60×0.37	7" REEL	10,000

Recommended Soldering Conditions



Package Outline Dimensions (DFN1006-2L)



Suggested Pad Layout

